

**TO-92MOD Plastic-Encapsulate Transistors****2SC1627A** TRANSISTOR (NPN)**FEATURE**

Power dissipation

 P_{CM} : 0.8 W ($T_{amb}=25^{\circ}C$)

Collector current

 I_{CM} : 0.4 A

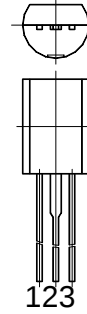
Collector-base voltage

 $V_{(BR)CBO}$: 80 V

Operating and storage junction temperature range

 T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$ **TO-92MOD**

1. EMITTER
2. COLLECTOR
3. BASE

**ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100\mu A, I_E = 0$	80		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 5mA, I_B = 0$	80		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100\mu A, I_C = 0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB} = 50V, I_E = 0$		0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V, I_C = 0$		0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 2V, I_C = 50mA$	70	240	
	$h_{FE(2)}$	$V_{CE} = 2V, I_C = 200mA$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 200mA, I_B = 20mA$		0.4	V
Base-emitter voltage	$V_{BE(on)}$	$V_{CE} = 2V, I_C = 5mA$	0.55	0.8	V
Transition frequency	f_T	$V_{CE} = 10V, I_C = 10mA$	80		MHz

CLASSIFICATION OF h_{FE} ⁽¹⁾

Rank	O	Y
Range	70-140	120-240